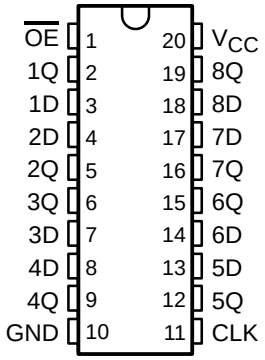
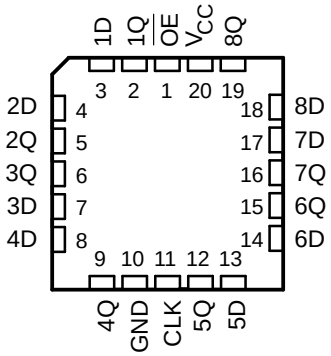
- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation**
- **High-Impedance State During Power Up and Power Down**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 500 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), and Thin Very Small-Outline (DGV) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Package, and Ceramic (J) DIPs**

SN54LVTH374 . . . J OR W PACKAGE
SN74LVTH374 . . . DB, DGV, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVTH374 . . . FK PACKAGE
(TOP VIEW)



description

These octal edge-triggered D-type flip-flops are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The ’LVTH374 feature 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. These devices are particularly suitable for implementing buffer registers, input/output (I/O) ports, bidirectional bus drivers, and working registers.

On the positive transition of the clock (CLK) input, the Q outputs are set to the logic levels at the data (D) inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect internal operations of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

description (continued)

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

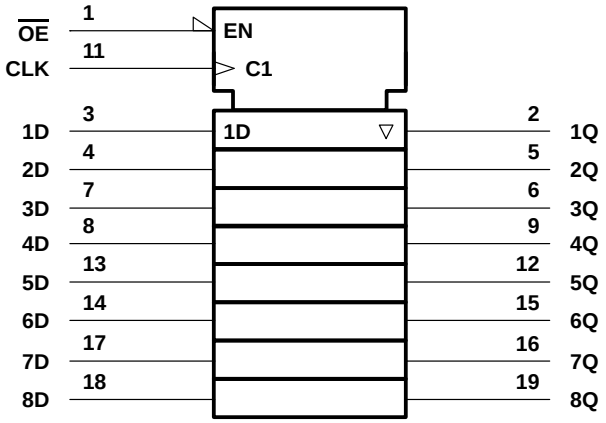
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN54LVTH374 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH374 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

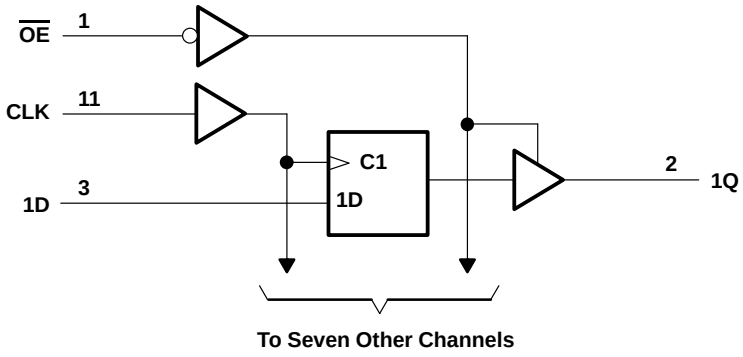
INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	H or L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) . . . . . –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTH374 . . . . . 96 mA
SN74LVTH374 . . . . . 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTH374 . . . . . 48 mA
SN74LVTH374 . . . . . 64 mA
Input clamp current, I_{IK} ($V_I < 0$) . . . . . –50 mA
Output clamp current, I_{OK} ($V_O < 0$) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package . . . . . 115°C/W
DGV package . . . . . 146°C/W
DW package . . . . . 97°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

		SN54LVTH374		SN74LVTH374		UNIT
		MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage	2		2		V
V_{IL}	Low-level input voltage		0.8		0.8	V
V_I	Input voltage		5.5		5.5	V
I_{OH}	High-level output current		–24		–32	mA
I_{OL}	Low-level output current		48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate	200		200		µs/V
T_A	Operating free-air temperature	–55	125	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVTH374			SN74LVTH374			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.7 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = –8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	µA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs‡	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0, V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	µA
I_{OZPU}§		V_{CC} = 0 to 1.5 V, V_O = 0.5 V to 3 V, $\overline{OE}$ = Don't care				±100			±100	µA
I_{OZPD}§		V_{CC} = 1.5 V to 0, V_O = 0.5 V to 3 V, $\overline{OE}$ = Don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			0.19			0.19	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.19	
ΔI_{CC}¶		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			3			3		pF
C_o		V_O = 3 V or 0			7			7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Unused pins at V_{CC} or GND
§ This parameter is warranted but not production tested.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

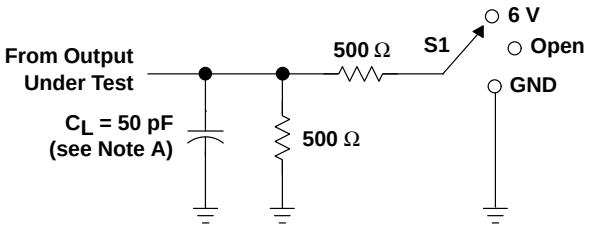
		SN54LVTH374				SN74LVTH374				UNIT
		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		160		160		160		160	MHz
t_w	Pulse duration, CLK high or low	3		3		3		3		ns
t_{su}	Setup time, data before CLK↑	1.6		2		1.5		2		ns
t_h	Hold time, data after CLK↑	0.8		0.5		0.8		0		ns

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTH374				SN74LVTH374					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}			160		160		160			160		MHz
t_{PLH}	CLK	Q	1.7	4.7		5.3	1.8	2.9	4.5		5	ns
t_{PHL}			1.7	4.5		4.6	1.8	2.9	4.2		4.3	
t_{PZH}	$\overline{OE}$	Q	1.2	4.9		5.7	1.3	2.8	4.7		5.6	ns
t_{PZL}			1.5	4.8		5.4	1.6	3	4.7		5.2	
t_{PHZ}	$\overline{OE}$	Q	1.8	4.8		5	1.9	3	4.6		4.9	ns
t_{PLZ}			1.9	4.9		5	2	3.1	4.5		4.6	

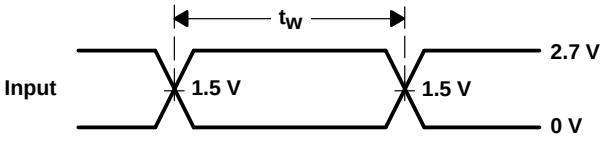
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

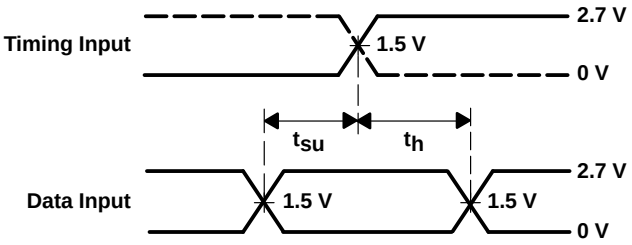


LOAD CIRCUIT

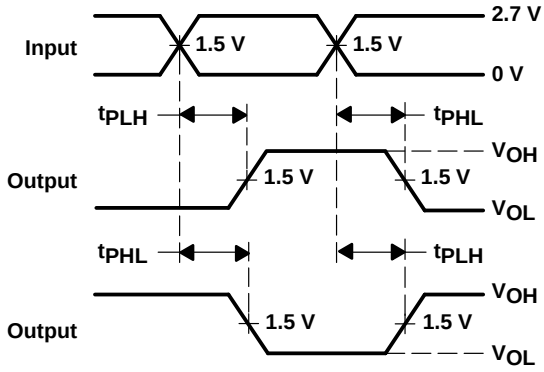
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



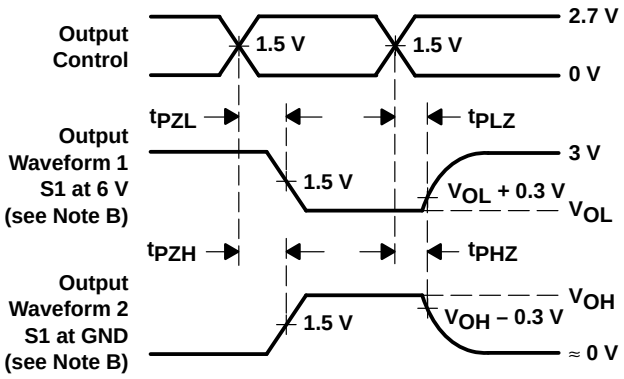
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

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